

# 2SA1368

FOR HIGH VOLTAGE DRIVE APPLICATION  
SILICON PNP EPITAXIAL TYPE

## DESCRIPTION

2SA1368 is a silicon PNP epitaxial type transistor. It is designed with high collector dissipation, high voltage.

Complementary with 2SC3438.

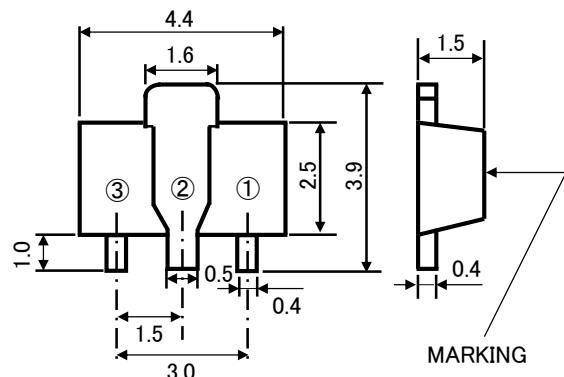
## FEATURE

- High voltage  $V_{CEO} = -100V$
- High peak collector current.  $I_{CM} = -800mA$
- High gain band width product.  $FT = 130MHz$  (typ)
- High collector dissipation.  $P_c = 500mW$
- Small package for easy mounting

## APPLICATION

For 20~40W amp complementary drive, relay drive, power supply application.

## OUTLINE DRAWING



UNIT:mm

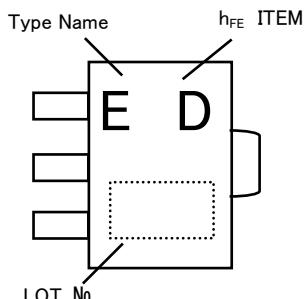
## TERMINAL CONNECTOR

①:BASE	JEITA:SC-62
②:COLLECTOR	JEDEC:SOT-89
③:EMITTER	

## MAXIMUM RATING ( $T_a=25^\circ C$ )

SYMBOL	PARAMETER	RATING	UNIT
$V_{CBO}$	Collector to Base voltage	-100	V
$V_{EBO}$	Emitter to Base voltage	-5	V
$V_{CEO}$	Collector to Emitter voltage	-100	V
$I_c$	Collector current	-500	mA
$I_{CM}$	Peak collector current	-800	mA
$P_c$	Collector dissipation	500	mW
$T_j$	Junction temperature	+150	°C
$T_{stg}$	Storage temperature	-55~+150	°C

## MARKING



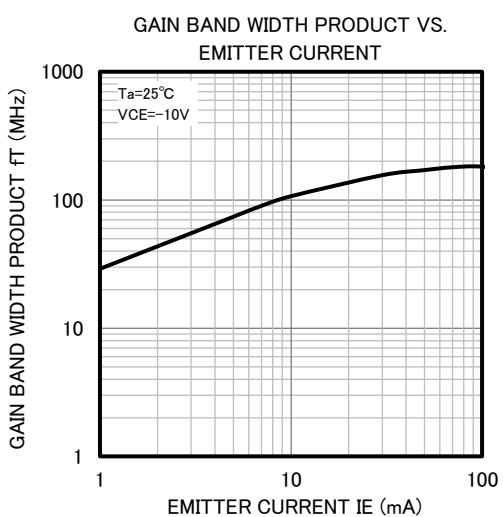
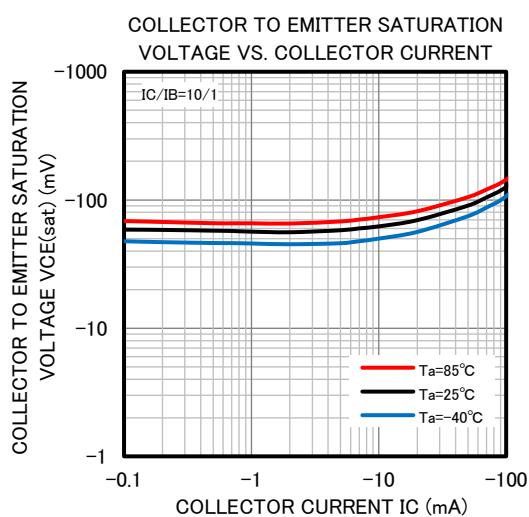
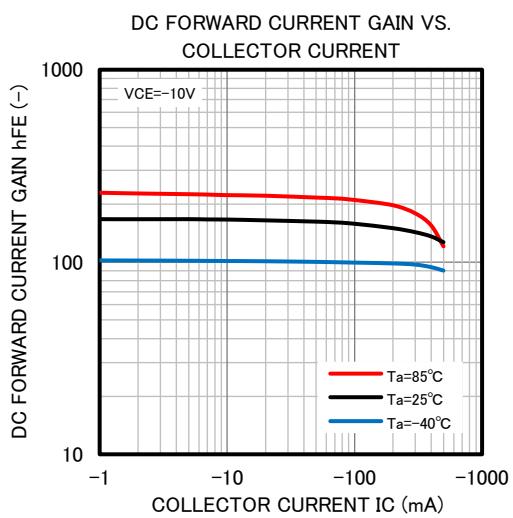
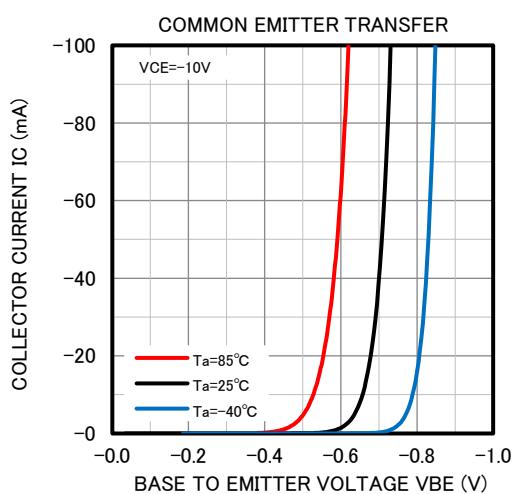
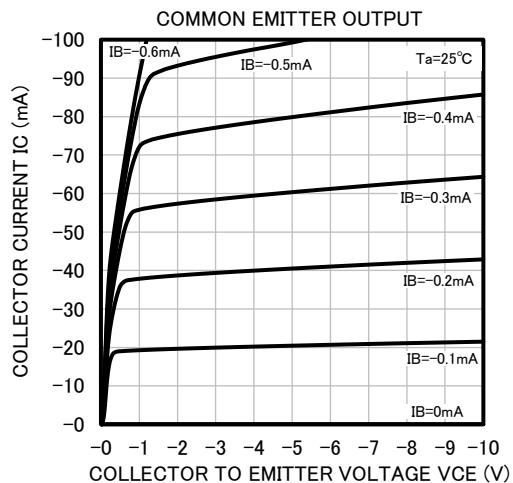
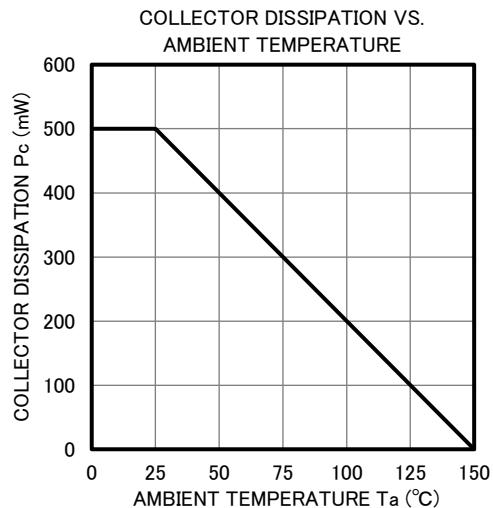
## ELECTRICAL CHARACTERISTICS ( $T_a=25^\circ C$ )

SYMBOL	PARAMETER	TEST CONDITIONS	LIMITS			UNIT
			MIN	TYP	MAX	
$V_{(BR)CBO}$	C to B breakdown voltage	$I_c = -10\mu A, I_E = 0mA$	-100	-	-	V
$V_{(BR)EBO}$	E to B breakdown voltage	$I_E = -10\mu A, I_c = 0mA$	-5	-	-	V
$V_{(BR)CEO}$	C to E breakdown voltage	$I_c = -1mA, R_{BE} = \infty$	-100	-	-	V
$I_{CBO}$	Collector cut off current	$V_{CB} = -50V, I_E = 0mA$	-	-	-0.5	$\mu A$
$I_{EBO}$	Emitter cut off current	$V_{EB} = -2V, I_c = 0mA$	-	-	-0.5	$\mu A$
$h_{FE} \times$	DC forward current gain	$V_{CE} = -10V, I_c = -10mA$	55	-	300	-
$V_{CE(sat)}$	C to E Saturation Voltage	$I_c = -150mA, I_B = -15mA$	-	-0.15	-0.5	V
$f_T$	Gain band width product	$V_{CE} = -10V, I_E = 10mA$	-	130	-	MHz
$C_{ob}$	Collector output capacitance	$V_{CB} = -10V, I_E = 0mA, f = 1MHz$	-	11	-	pF

※) It shows  $h_{FE}$  classification at right table.

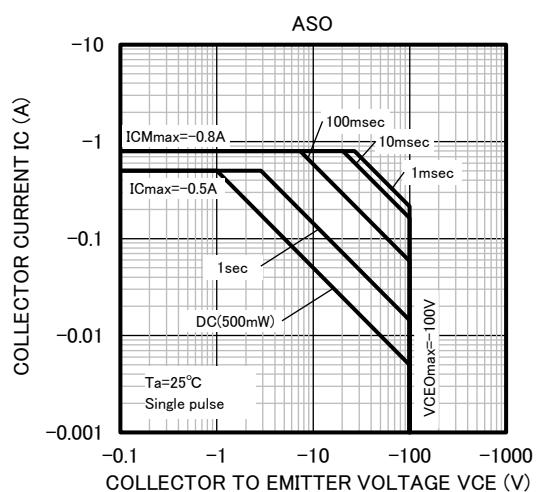
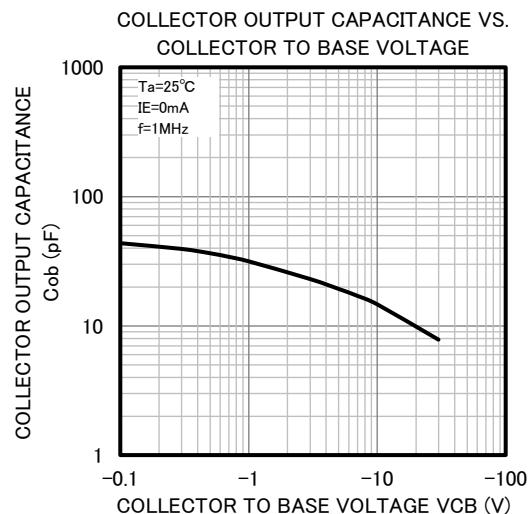
Item	C	D	E
$h_{FE}$	55~110	90~180	150~300

## TYPICAL CHARACTERISTICS



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